



## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

$V_{DS}$	60V
$I_D$	220A
$R_{DS(ON)}$ ( at $V_{GS}=10V$ )	3m
$R_{DS(ON)}$ ( at $V_{GS}=6V$ )	4m
100% EAS Tested	
100% $V_{DS}$ Tested	

### General Description

Double trench MOSFET technology  
Excellent package for heat dissipation  
High density cell design for low  $R_{DS(ON)}$   
Epoxy Meets UL 94 V-0 Flammability Rating  
Halogen Free  
Moisture Sensitivity Level 1

### Applications

High Power switching application  
BMS



# YJT220G06H

## Electrical Characteristics ( $T_J=25$ unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	
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## Typical Electrical and Thermal Characteristics Diagrams

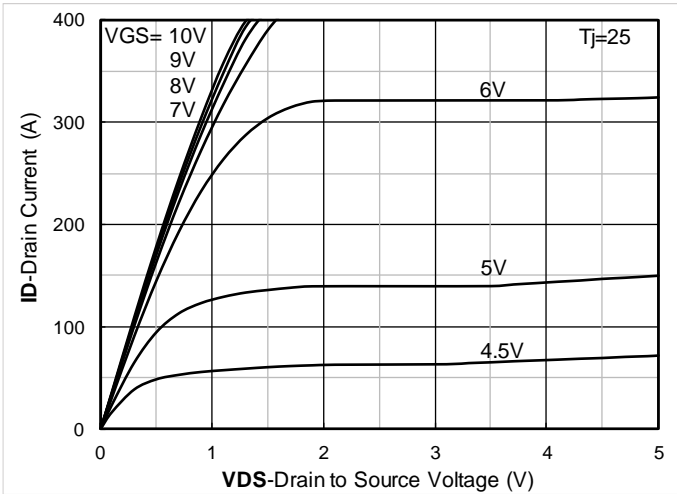


Figure 1. Output Characteristics

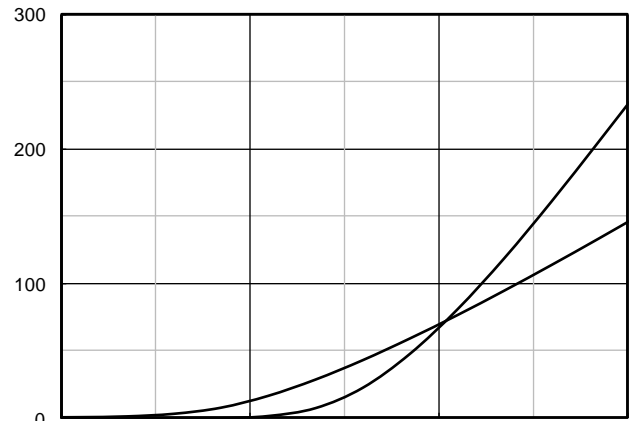


Figure 2. Transfer Characteristics

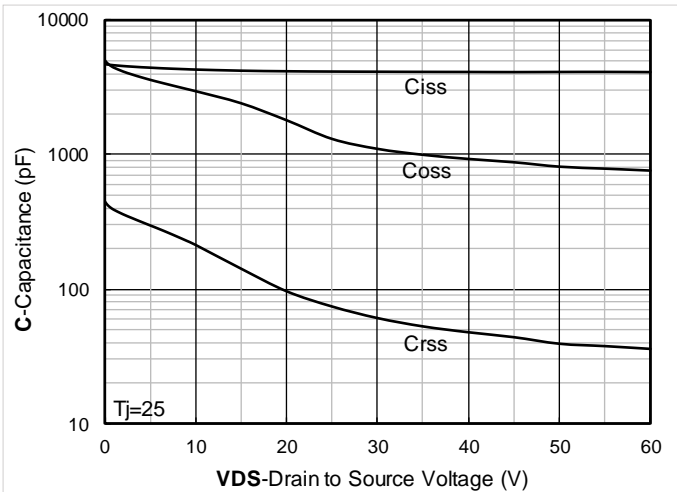


Figure 3. Capacitance Characteristics

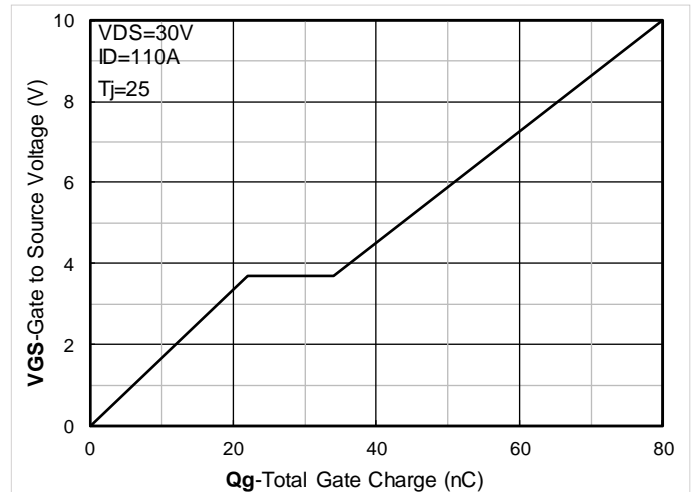


Figure 4. Gate Charge

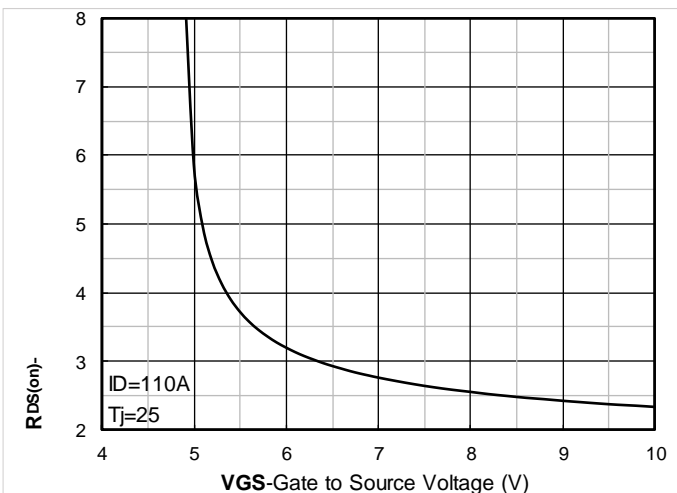


Figure 5. On-Resistance vs Gate to Source Voltage

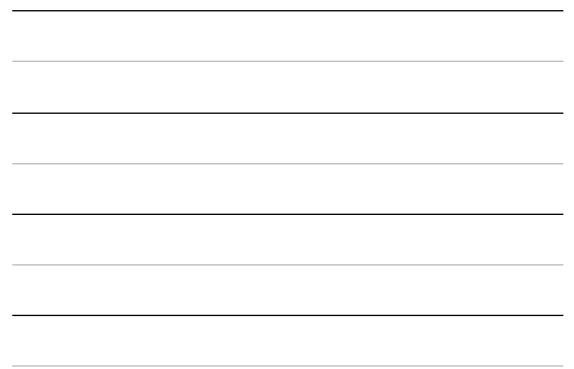


Figure 6. Normalized On-Resistance



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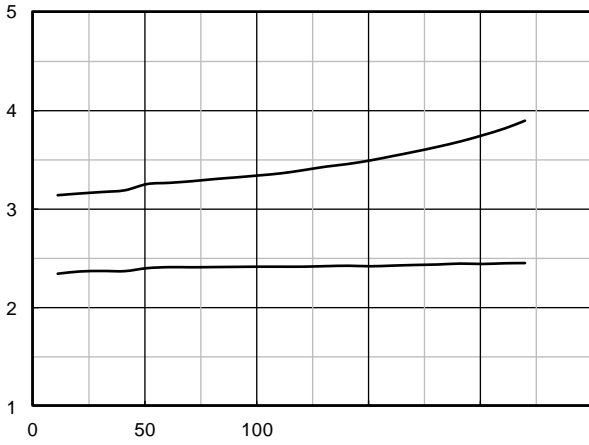


Figure 7.  $R_{DS(on)}$  VS Drain Current

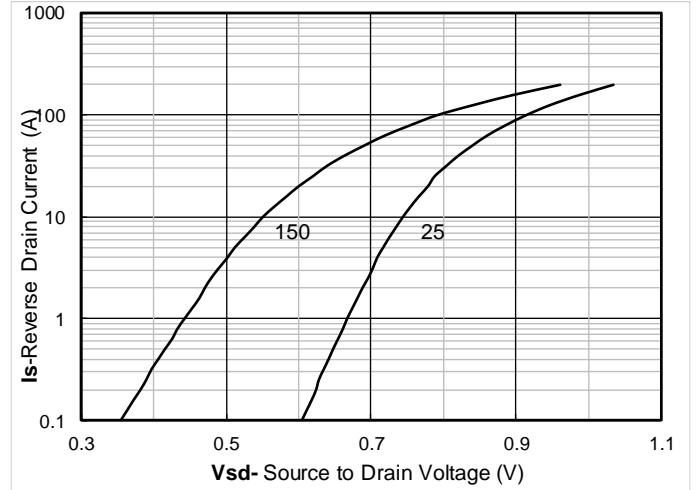


Figure 8. Forward characteristics of reverse diode

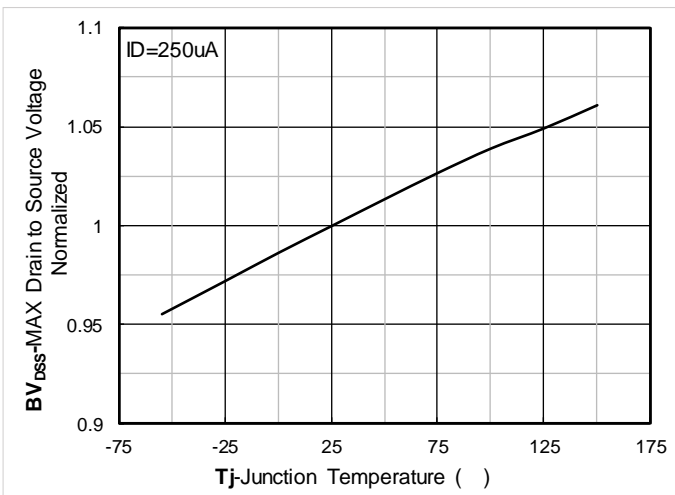


Figure 9. Normalized breakdown voltage

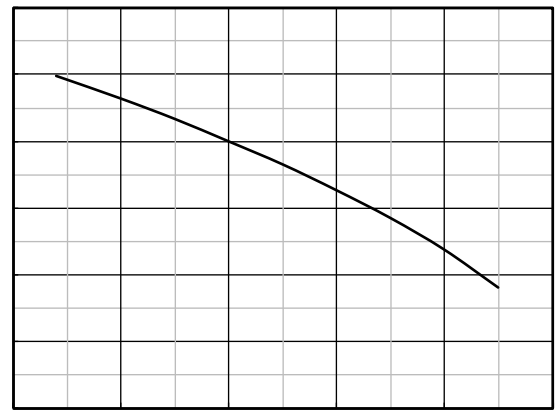


Figure 10. Normalized Threshold voltage

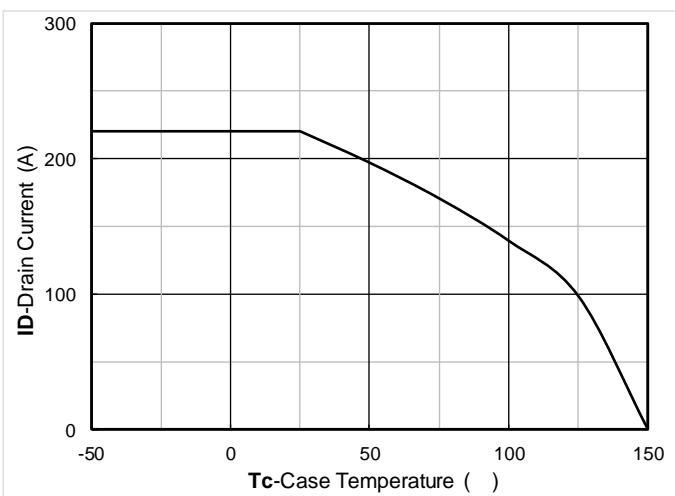


Figure 11. Current dissipation

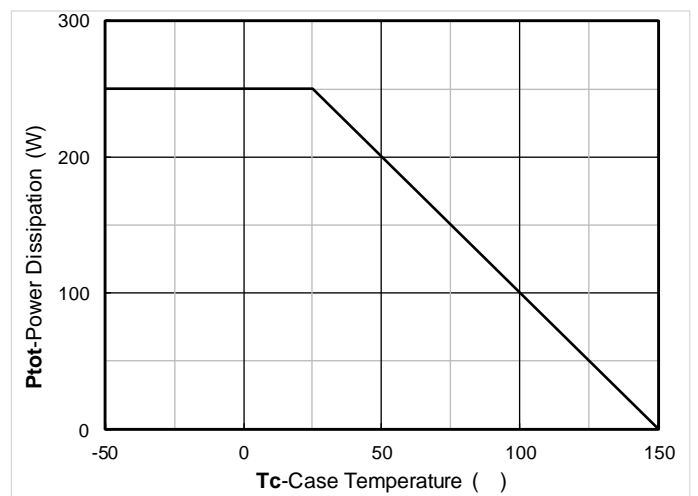


Figure 12. Power dissipation

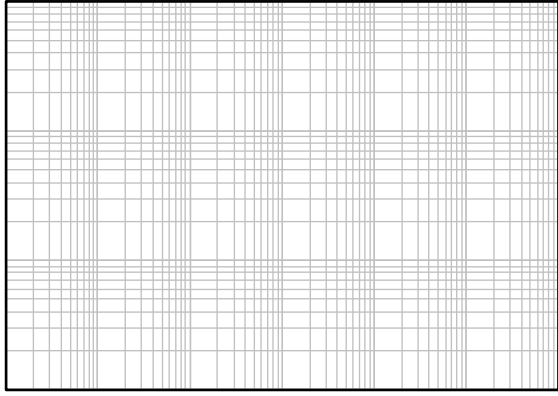


Figure 13. Maximum Transient Thermal Impedance

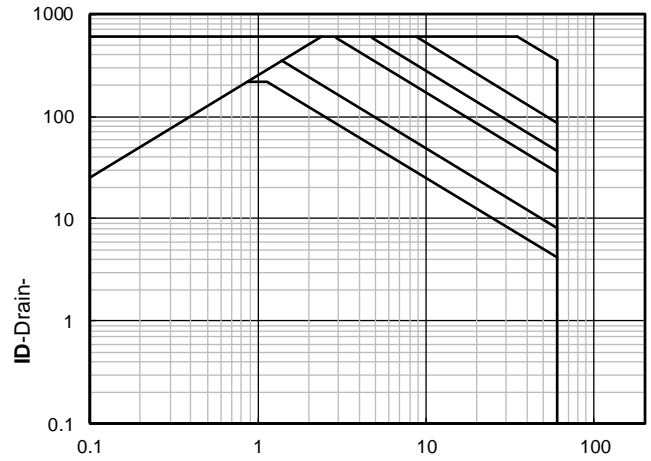


Figure 14. Safe Operation Area

## Test Circuits & Waveforms

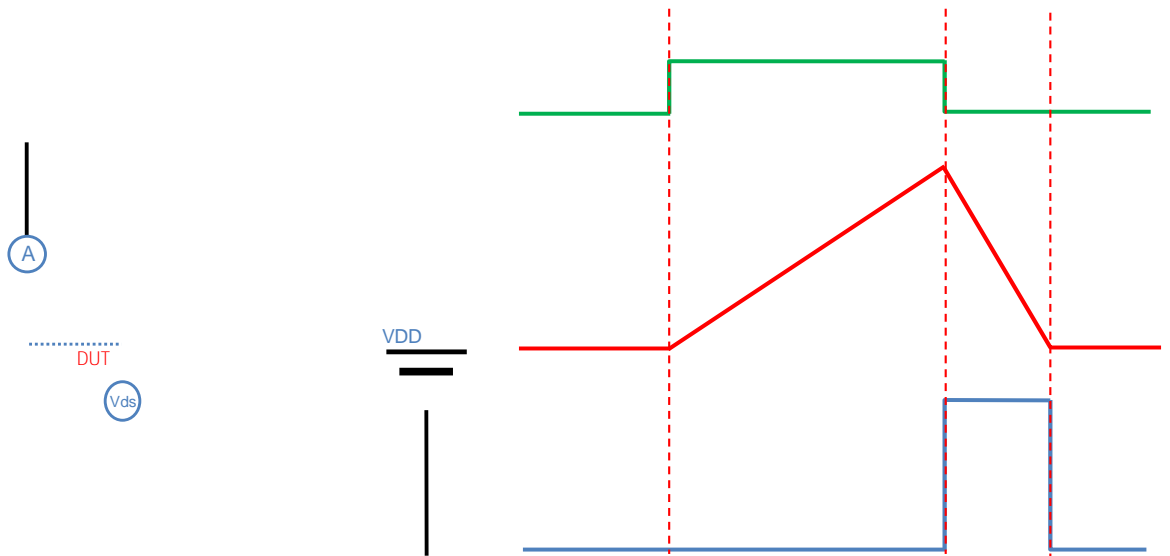


Figure A. Unclamped Inductive Switching (UIS) Test Circuit & Waveform



Figure B. Gate Charge Test Circuit & Waveform

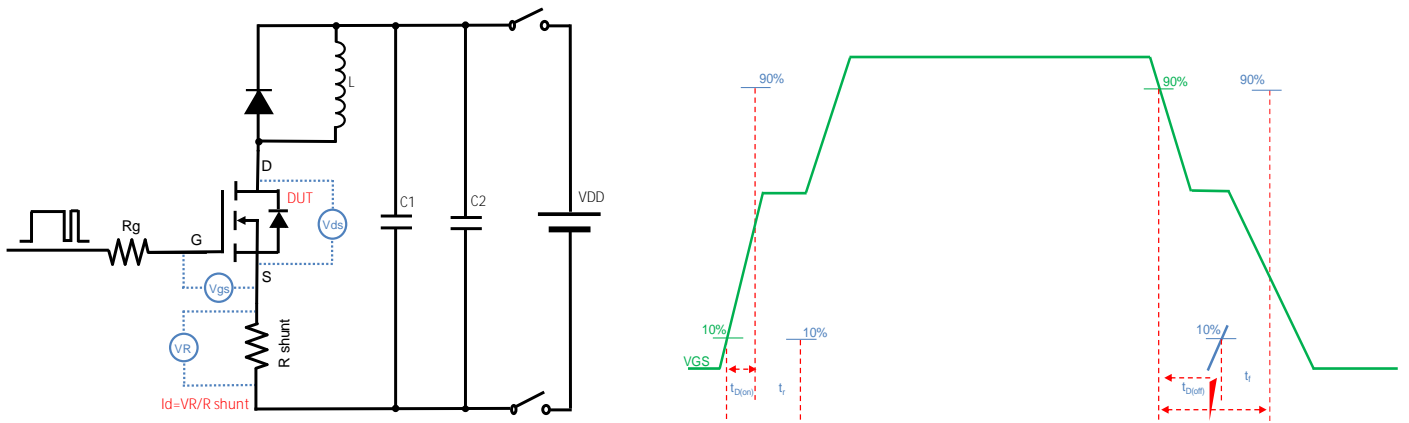


Figure C. Resistive Switching Test Circuit & Waveform

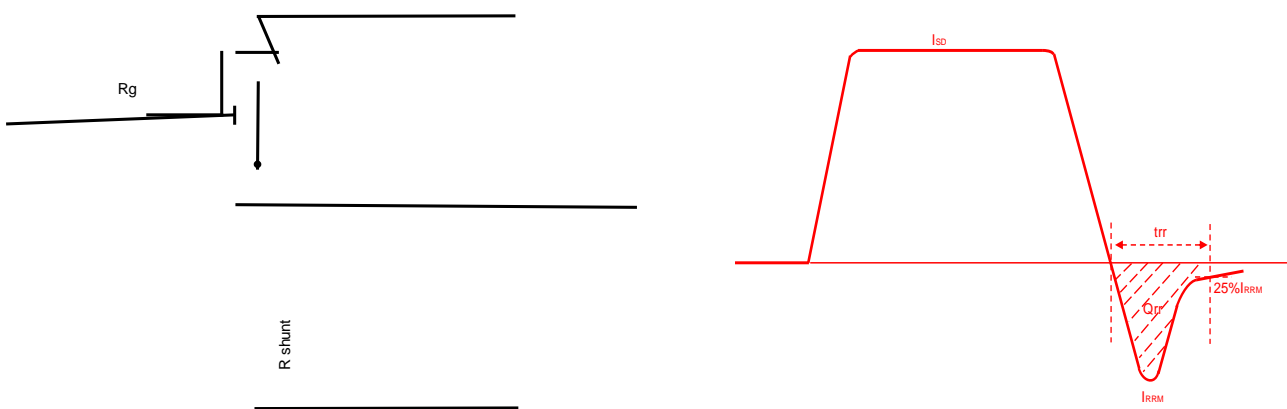


Figure D. Diode Recovery Test Circuit & Waveform



**TOLL Package information**



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## Disclaimer

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